



IPP111N15N3 G Information



For Reference Only

Part Number IPP111N15N3 G

Manufacturer Infineon Technologies

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 150V 83A TO220-3

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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IPP111N15N3 G Specifications

Manufacturer Part Number IPP111N15N3 G Manufacturer Infineon Technologies Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Series OptiMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 150V Current - Continuous Drain (Id) @ 25°C 83A (Tc) Drive Voltage (Max Rds On, Min Rds On) 8V, 10V Vgs(th) (Max) @ Id 4V @ 160µA Gate Charge (Qg) (Max) @ Vgs 55nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 3230pF @ 75V Vgs (Max) 20V FET Feature - Power Dissipation (Max) 214W (Tc) Rds On (Max) @ Id, Vgs 11.1 mOhm @ 83A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO-220-3 Package / Case TO-220-3 Report errors? Report errors?		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Series OptiMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 83A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Spinut Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 11.1 mOhm @ 83A, 10V Operating Temperature Mounting Type Supplier Device Package PG-TO-220-3 Package / Case TO-220-3	Manufacturer Part Number	IPP111N15N3 G
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Series OptiMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 150V Current - Continuous Drain (Id) @ 25°C 83A (Tc) Drive Voltage (Max Rds On, Min Rds On) 8V, 10V Vgs(th) (Max) @ Id 4V @ 160µA Gate Charge (Qg) (Max) @ Vgs 55nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 3230pF @ 75V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 214W (Tc) Rds On (Max) @ Id, Vgs 11.1 mOhm @ 83A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO-220-3 Package / Case TO-220-3		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)150VCurrent - Continuous Drain (Id) @ 25°C83A (Tc)Drive Voltage (Max Rds On, Min Rds On)8V, 10VVgs(th) (Max) @ Id4V @ 160μAGate Charge (Qg) (Max) @ Vgs55nC @ 10VInput Capacitance (Ciss) (Max) @ Vds3230pF @ 75VVgs (Max)±20VFET Feature-Power Dissipation (Max)214W (Tc)Rds On (Max) @ Id, Vgs11.1 mOhm @ 83A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO-220-3Package / CaseTO-220-3	Package	TO-220-3
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 83A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 4V @ 160μA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 11.1 mOhm @ 83A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Supplier Device Package PG-TO-220-3 Package / Case MOSFET (Metal Oxide) 150V MOSFET (Metal Oxide) 150V 83A (Tc) 83A (Tc) 83A (Tc) 83A (Tc) 83A (Tc) 84V @ 160μA 4V @ 160μA 55nC @ 10V 11.1 mOhm 83A, 10V 11.1 mOhm @ 83A, 10V	Series	OptiMOS?
Drain to Source Voltage (Vdss)150 VCurrent - Continuous Drain (Id) @ 25°C83A (Tc)Drive Voltage (Max Rds On, Min Rds On)8V, 10 VVgs(th) (Max) @ Id4V @ 160 μAGate Charge (Qg) (Max) @ Vgs55nC @ 10 VInput Capacitance (Ciss) (Max) @ Vds3230 pF @ 75 VVgs (Max)±20 VFET Feature-Power Dissipation (Max)214W (Tc)Rds On (Max) @ Id, Vgs11.1 mOhm @ 83A, 10 VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO-220-3Package / CaseTO-220-3	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C 83A (Tc) Drive Voltage (Max Rds On, Min Rds On) 8V, 10V Vgs(th) (Max) @ Id 4V @ 160μA Gate Charge (Qg) (Max) @ Vgs 55nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 3230pF @ 75V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 214W (Tc) Rds On (Max) @ Id, Vgs 11.1 mOhm @ 83A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO-220-3 Package / Case TO-220-3	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)8V, 10VVgs(th) (Max) @ Id4V @ 160μAGate Charge (Qg) (Max) @ Vgs55nC @ 10VInput Capacitance (Ciss) (Max) @ Vds3230pF @ 75VVgs (Max)±20VFET Feature-Power Dissipation (Max)214W (Tc)Rds On (Max) @ Id, Vgs11.1 mOhm @ 83A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO-220-3Package / CaseTO-220-3	Drain to Source Voltage (Vdss)	150V
Vgs(th) (Max) @ Id 4V @ 160μA Gate Charge (Qg) (Max) @ Vgs 55nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 3230pF @ 75V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 214W (Tc) Rds On (Max) @ Id, Vgs 11.1 mOhm @ 83A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO-220-3 Package / Case TO-220-3	Current - Continuous Drain (Id) @ 25°C	83A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) +20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 11.1 mOhm @ 83A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO-220-3 Package / Case TO-220-3	Drive Voltage (Max Rds On, Min Rds On)	8V, 10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 11.1 mOhm @ 83A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO-220-3 Package / Case TO-220-3	Vgs(th) (Max) @ Id	4V @ 160μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)214W (Tc)Rds On (Max) @ Id, Vgs11.1 mOhm @ 83A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO-220-3Package / CaseTO-220-3	Gate Charge (Qg) (Max) @ Vgs	55nC @ 10V
FET Feature - Power Dissipation (Max) 214W (Tc) Rds On (Max) @ Id, Vgs 11.1 mOhm @ 83A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO-220-3 Package / Case TO-220-3	Input Capacitance (Ciss) (Max) @ Vds	3230pF @ 75V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 11.1 mOhm @ 83A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO-220-3 Package / Case TO-220-3	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs 11.1 mOhm @ 83A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO-220-3 Package / Case TO-220-3	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO-220-3 Package / Case TO-220-3	Power Dissipation (Max)	214W (Tc)
Mounting Type Through Hole Supplier Device Package PG-TO-220-3 Package / Case TO-220-3	Rds On (Max) @ Id, Vgs	11.1 mOhm @ 83A, 10V
Supplier Device Package PG-TO-220-3 Package / Case TO-220-3	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-220-3	Mounting Type	Through Hole
-	Supplier Device Package	PG-TO-220-3
Report errors?	Package / Case	TO-220-3
		Report errors?

IPP111N15N3 G Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IPP111N15N3 G Payment Methods



















IPP111N15N3 G Shipping Methods













If you have any question about IPP111N15N3 G, please do not hesitate to contact us!

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